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General Description:

Npn phototransistor; pn infrared emitting diode; gallium arsenide led; silicon photo darlington transistor; 250 mw; 80 ma; 30 volts; minus 55 degrees c to plus 100 degrees c operating junction temperature range; 6 terminals; 0.350 in. Lg; 0.300 in. W; 0.200 in. H

Specification Data:

80131-release 6464 professional/industrial association specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fig:

A23900